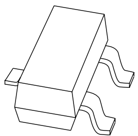


PBRP113ET

PNP 800 mA, 40 V BISS RET; R1 = 1 kΩ, R2 = 1 kΩ

Rev. 01 — 17 December 2007 Product data sheet

1. Product profile

1.1 General description

800 mA PNP low V_{CEsat} Breakthrough In Small Signal (BISS) Resistor-Equipped Transistor (RET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBRN113ET.

1.2 Features

- 800 mA repetitive peak output current
- High current gain h_{FE}
- Built-in bias resistors
- Simplifies circuit design
- Low collector-emitter saturation voltage V_{CEsat}
- Reduces component count
- Reduces pick and place costs
- ±10 % resistor ratio tolerance

1.3 Applications

- Digital application in automotive and industrial segments
- Medium current peripheral driver
- Switching loads

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	–40	V
I_O	output current		[1][2]	-	-	–600	mA
I_{ORM}	repetitive peak output current	$t_p \leq 1$ ms; $\delta \leq 0.33$	[3]	-	-	–800	mA
R1	bias resistor 1 (input)			0.7	1	1.3	kΩ
R2/R1	bias resistor ratio			0.9	1	1.1	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for collector 1 cm^2.

[2] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	input (base)		
2	GND (emitter)		
3	output (collector)		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBRP113ET	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBRP113ET	*7K

[1] * = -: made in Hong Kong
* = p: made in Hong Kong
* = t: made in Malaysia
* = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	–40	V
V_{CEO}	collector-emitter voltage	open base		-	–40	V
V_{EBO}	emitter-base voltage	open collector		-	–10	V
V_I	input voltage					
	positive			-	+10	V
	negative			-	–10	V
I_O	output current		[1][2]	-	–600	mA
I_{ORM}	repetitive peak output current	$t_p \leq 1$ ms; $\delta \leq 0.33$	[3]	-	–800	mA

© NXP B.V. 2007. All rights reserved.

Table 5. Limiting values *...continued*

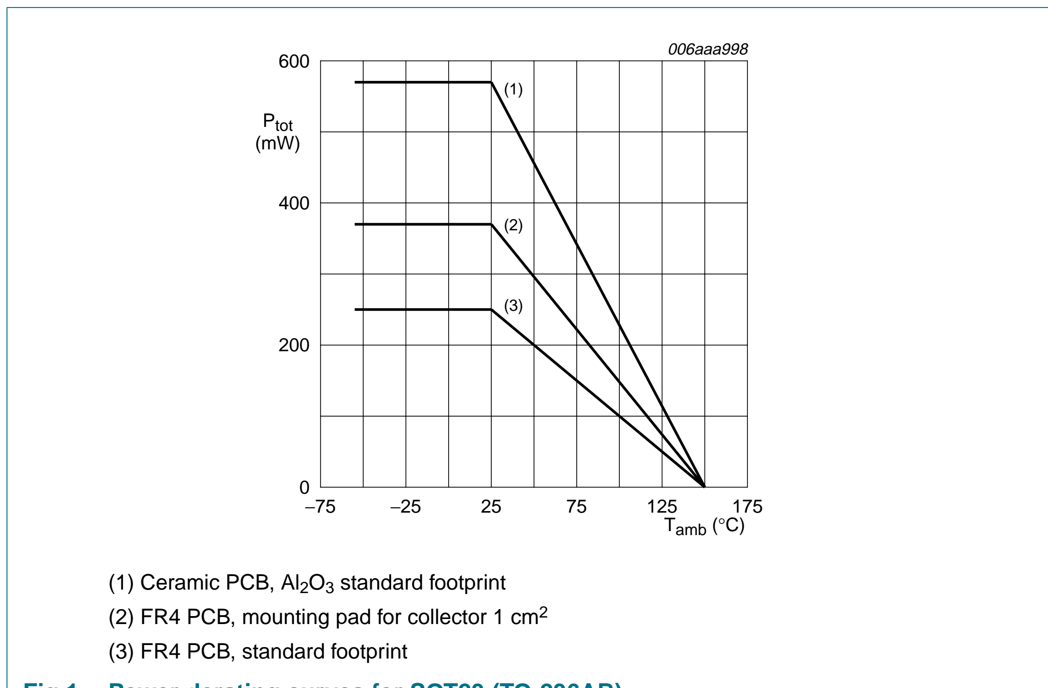
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C				
			[3]	-	250	mW
			[1]	-	370	mW
			[2]	-	570	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			–55	+150	°C
T_{stg}	storage temperature			–65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm^2.

[2] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



(1) Ceramic PCB, Al_2O_3 standard footprint

(2) FR4 PCB, mounting pad for collector 1 cm^2

(3) FR4 PCB, standard footprint

Fig 1. Power derating curves for SOT23 (TO-236AB)

© NXP B.V. 2007. All rights reserved.

6. Thermal characteristics

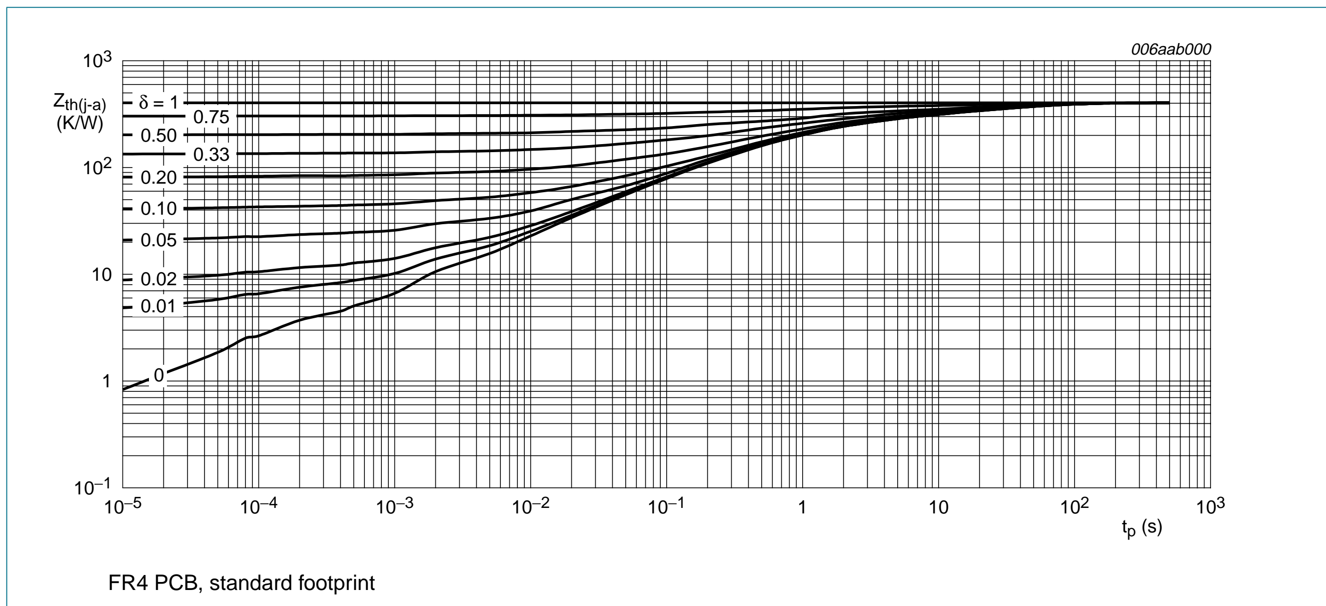
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air					
			[1]	-	-	500	K/W
			[2]	-	-	338	K/W
			[3]	-	-	219	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	105	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm^2.

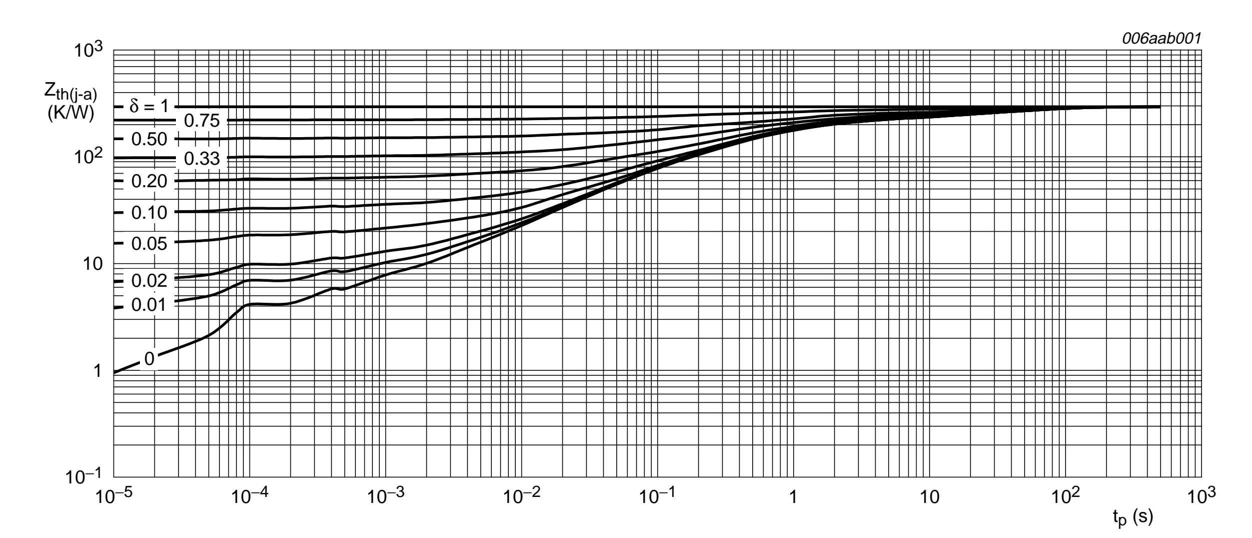
[3] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.



FR4 PCB, standard footprint

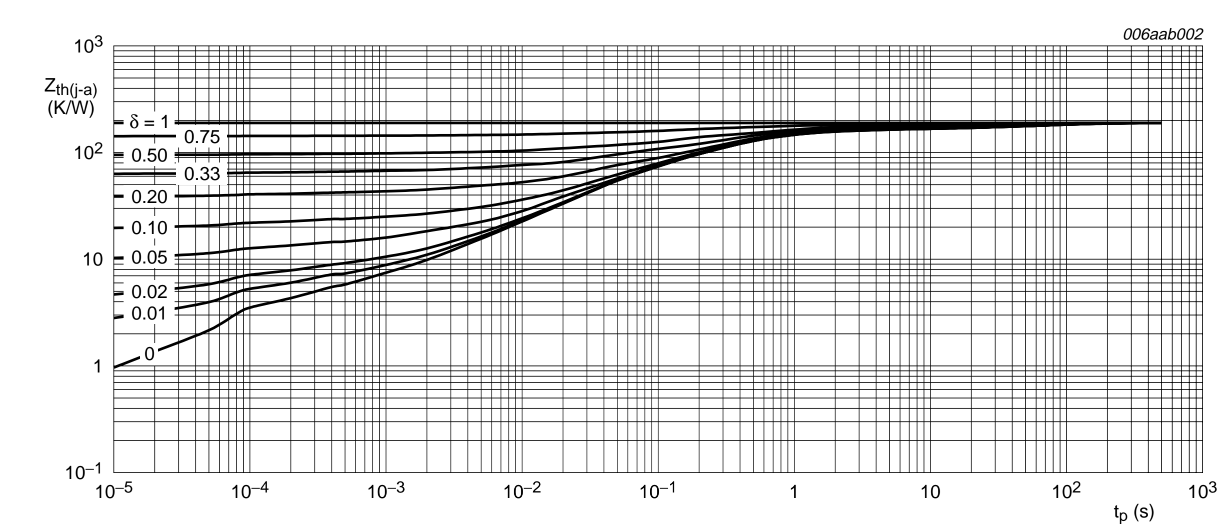
Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB); typical values

© NXP B.V. 2007. All rights reserved.



FR4 PCB, mounting pad for collector 1 cm^2

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB); typical values



Ceramic PCB, Al_2O_3 standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB); typical values

© NXP B.V. 2007. All rights reserved.

7. Characteristics

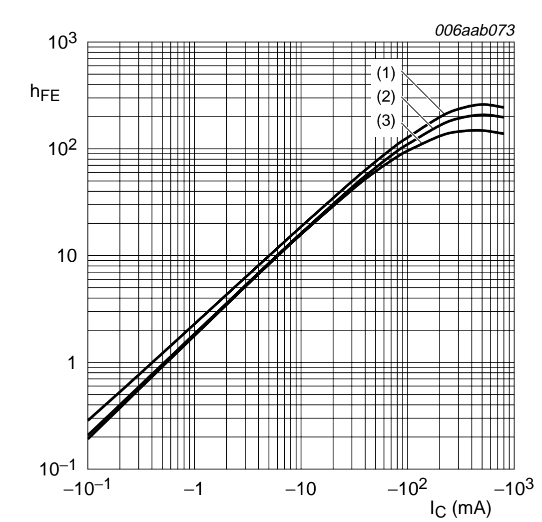
Table 7. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = −30 V; I_E = 0 A		-	-	−100	nA
I_{CEO}	collector-emitter cut-off current	V_{CE} = −30 V; I_B = 0 A		-	-	−0.5	µA
I_{EBO}	emitter-base cut-off current	V_{EB} = −5 V; I_C = 0 A		-	-	−4	mA
h_{FE}	DC current gain	V_{CE} = −5 V; I_C = −50 mA		40	65	-	
		V_{CE} = −5 V; I_C = −300 mA	[1]	130	190	-	
		V_{CE} = −5 V; I_C = −600 mA	[1]	140	210	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = −50 mA; I_B = −2.5 mA		-	−35	−45	mV
		I_C = −200 mA; I_B = −10 mA		-	−70	−100	mV
		I_C = −500 mA; I_B = −10 mA	[1]	-	−200	−300	mV
		I_C = −600 mA; I_B = −6 mA	[1]	-	−450	−750	mV
$V_{I(off)}$	off-state input voltage	V_{CE} = −5 V; I_C = −100 µA		−0.6	−1	−1.5	V
$V_{I(on)}$	on-state input voltage	V_{CE} = −0.3 V; I_C = −20 mA		−1	−1.3	−1.8	V
R1	bias resistor 1 (input)			0.7	1	1.3	kΩ
R2/R1	bias resistor ratio			0.9	1	1.1	
C_c	collector capacitance	V_{CB} = −10 V; I_E = i_e = 0 A; f = 1 MHz		-	11	-	pF

[1] Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.

© NXP B.V. 2007. All rights reserved.



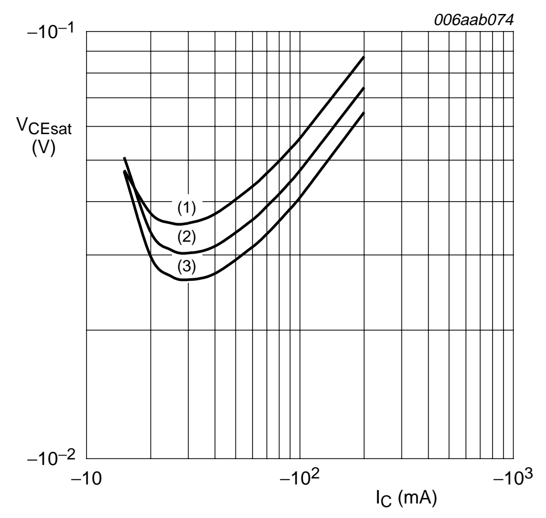
V_{CE} = −5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 5. DC current gain as a function of collector current; typical values



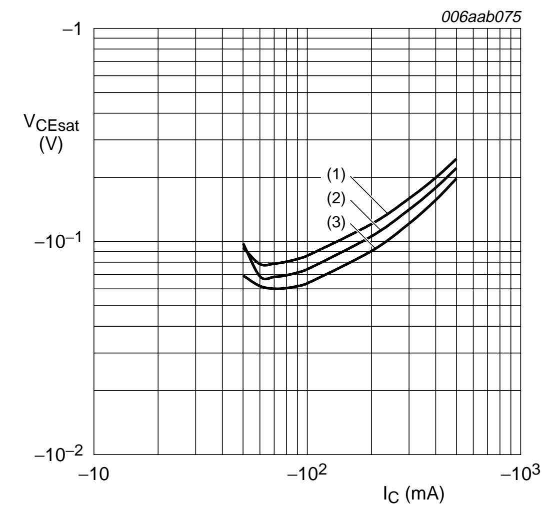
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values



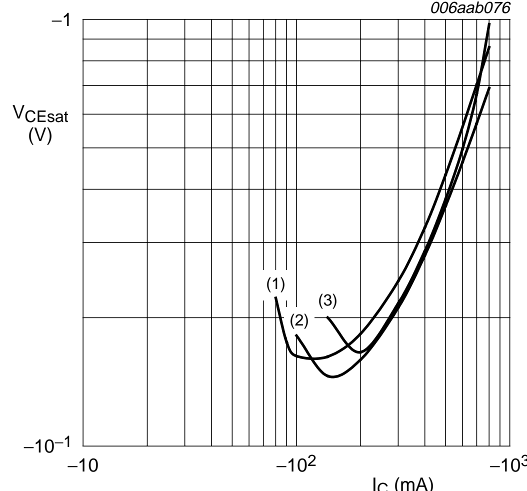
I_C/I_B = 50

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



I_C/I_B = 100

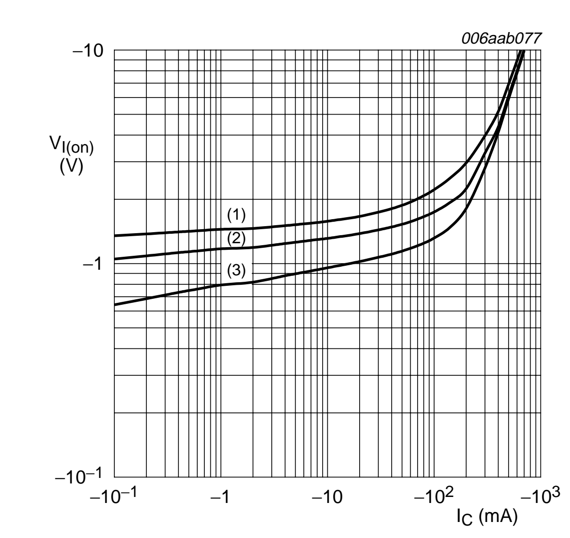
(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

© NXP B.V. 2007. All rights reserved.



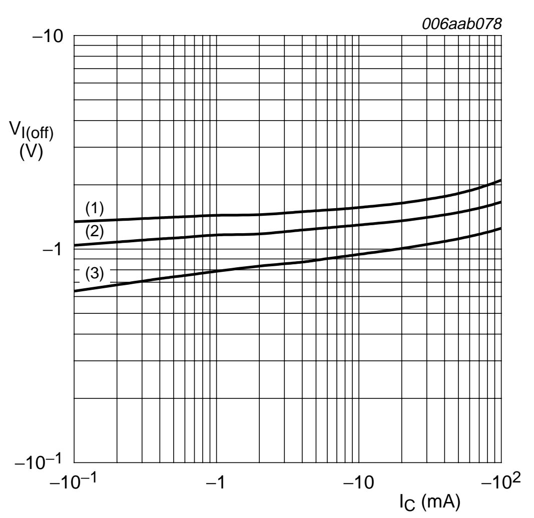
V_{CE} = −0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 9. On-state input voltage as a function of collector current; typical values



V_{CE} = −5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 10. Off-state input voltage as a function of collector current; typical values

8. Package outline

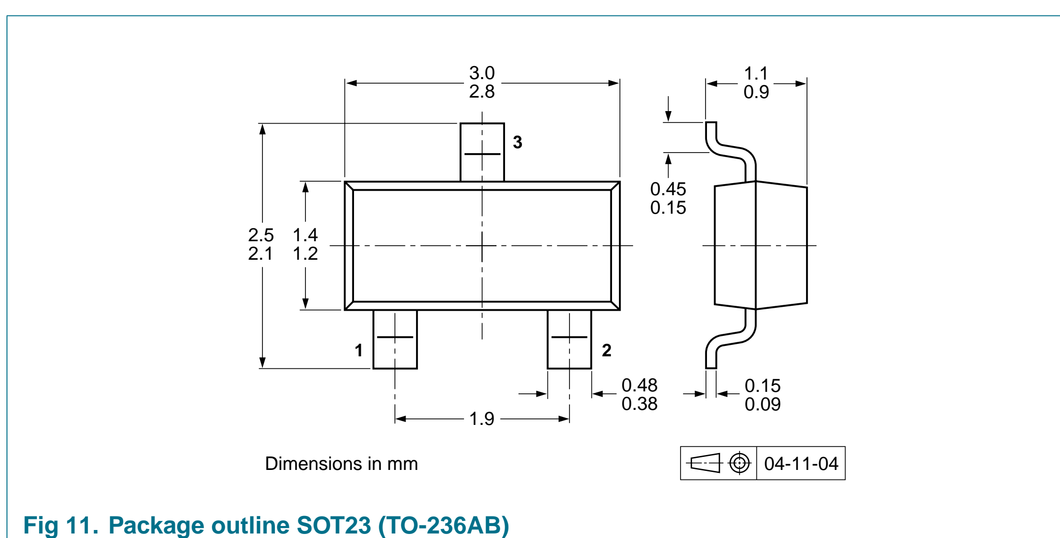


Fig 11. Package outline SOT23 (TO-236AB)

© NXP B.V. 2007. All rights reserved.

9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PBRP113ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 13.

10. Soldering

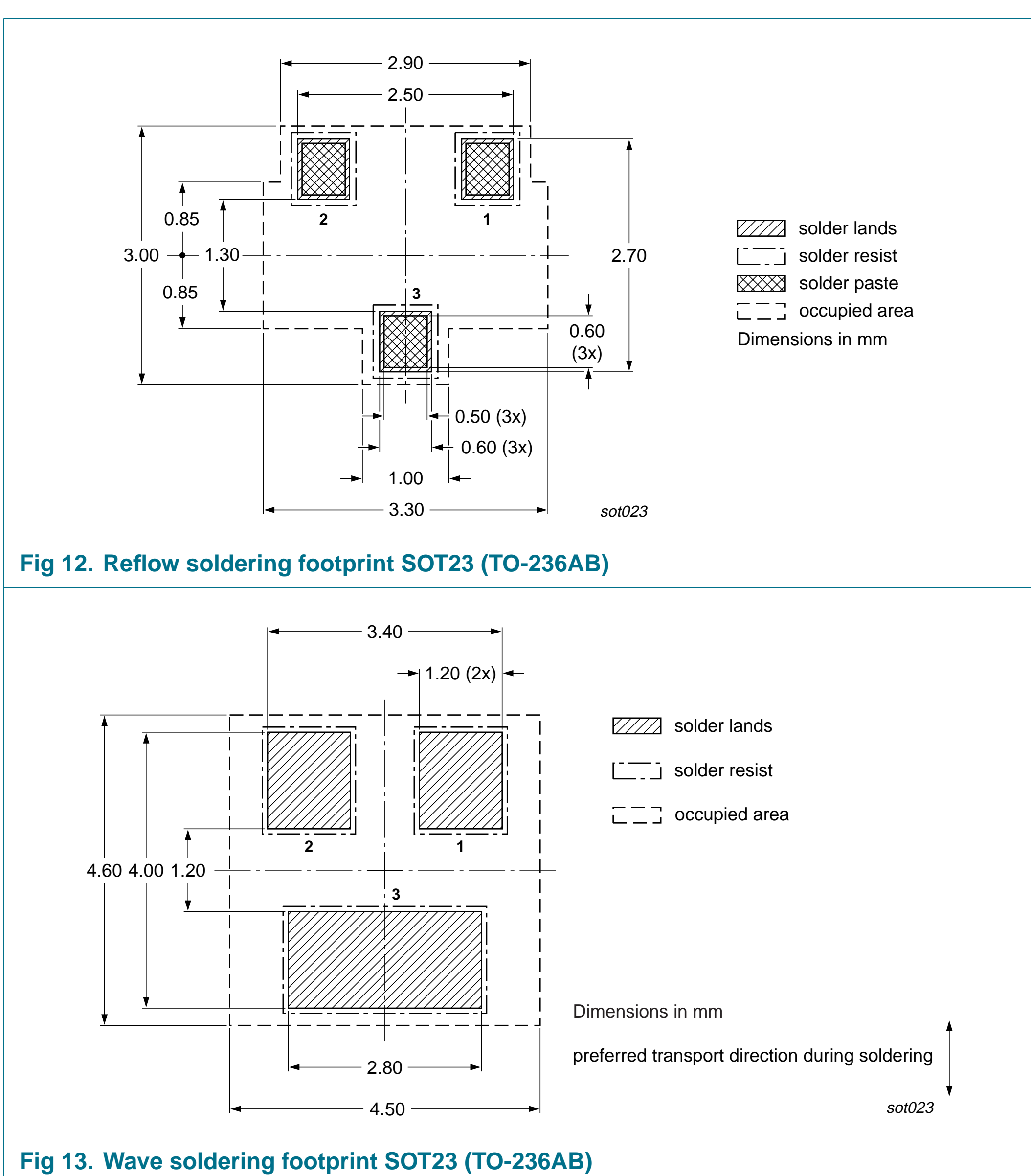


Fig 12. Reflow soldering footprint SOT23 (TO-236AB)

Fig 13. Wave soldering footprint SOT23 (TO-236AB)

© NXP B.V. 2007. All rights reserved.

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBRP113ET_1	20071217	Product data sheet	-	-

© NXP B.V. 2007. All rights reserved.

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

12.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

13. Contact information

For additional information, please visit: **http://www.nxp.com**

For sales office addresses, send an email to: **salesaddresses@nxp.com**

© NXP B.V. 2007. All rights reserved.

14. Contents

1 Product profile 1
1.1 General description. 1
1.2 Features 1
1.3 Applications 1
1.4 Quick reference data. 1
2 Pinning information 2
3 Ordering information 2
4 Marking 2
5 Limiting values. 2
6 Thermal characteristics. 4
7 Characteristics. 6
8 Package outline 8
9 Packing information. 9
10 Soldering 9
11 Revision history 10
12 Legal information. 11
12.1 Data sheet status 11
12.2 Definitions. 11
12.3 Disclaimers 11
12.4 Trademarks. 11
13 Contact information. 11
14 Contents 12

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2007. All rights reserved.

For more information, please visit: http://www.nxp.com
For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 17 December 2007

Document identifier: PBRP113ET_1